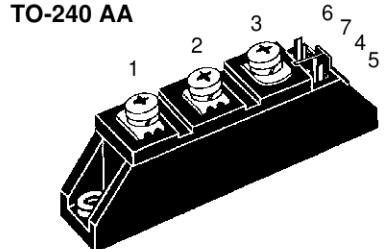


# Thyristor Modules

## Thyristor/Diode Modules

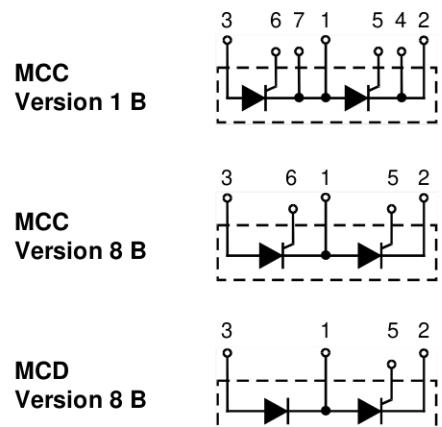
**I<sub>TRMS</sub> = 2x 50 A**  
**I<sub>TAVM</sub> = 2x 32 A**  
**V<sub>RRM</sub> = 800-1600 V**

V <sub>RSM</sub> V <sub>DSM</sub>	V <sub>RRM</sub> V <sub>DRM</sub>	Type	Version 1 B	Version 8 B	Version 8 B
900	800	MCC 26-08io1 B	MCC 26-08io8 B	MCD 26-08io8 B	
1300	1200	MCC 26-12io1 B	MCC 26-12io8 B	MCD 26-12io8 B	
1500	1400	MCC 26-14io1 B	MCC 26-14io8 B	MCD 26-14io8 B	
1700	1600	MCC 26-16io1 B	MCC 26-16io8 B	MCD 26-16io8 B	



Symbol	Test Conditions		Maximum Ratings	
I <sub>TRMS</sub> , I <sub>FRMS</sub>	T <sub>VJ</sub> = T <sub>VJM</sub>		50	A
I <sub>TAVM</sub> , I <sub>FAVM</sub>	T <sub>C</sub> = 75°C; 180° sine		32	A
	T <sub>C</sub> = 85°C; 180° sine		27	A
I <sub>TSM</sub> , I <sub>FSM</sub>	T <sub>VJ</sub> = 45°C; V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	520	A
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	460	A
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	500	A
i <sup>2</sup> dt	T <sub>VJ</sub> = 45°C V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1350	A <sup>2</sup> s
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1300	A <sup>2</sup> s
(di/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> f = 50 Hz, t <sub>p</sub> = 200 μs V <sub>D</sub> = 2/3 V <sub>DRM</sub> I <sub>G</sub> = 0.45 A di <sub>G</sub> /dt = 0.45 A/μs	repetitive, I <sub>T</sub> = 45 A  non repetitive, I <sub>T</sub> = I <sub>TAVM</sub>	150	A/μs
(dv/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> ; R <sub>GH</sub> = ∞; method 1 (linear voltage rise)	V <sub>DR</sub> = 2/3 V <sub>DRM</sub>	1000	V/μs
P <sub>GM</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> I <sub>T</sub> = I <sub>TAVM</sub>	t <sub>p</sub> = 30 μs t <sub>p</sub> = 300 μs	10 5	W
P <sub>GAV</sub>			0.5	W
V <sub>RGM</sub>			10	V
T <sub>VJ</sub>			-40...+125	°C
T <sub>VJM</sub>			125	°C
T <sub>stg</sub>			-40...+125	°C
V <sub>ISOL</sub>	50/60 Hz, RMS I <sub>ISOL</sub> ≤ 1 mA	t = 1 min t = 1 s	3000 3600	V~
M <sub>d</sub>	Mounting torque (M5) Terminal connection torque (M5)		2.5-4.0/22-35 Nm/lb.in. 2.5-4.0/22-35 Nm/lb.in.	
Weight	Typical including screws		90	g

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.  
IXYS reserves the right to change limits, test conditions and dimensions



### Features

- International standard package, JEDEC TO-240 AA
- Direct copper bonded Al<sub>2</sub>O<sub>3</sub>-ceramic base plate
- Planar passivated chips
- Isolation voltage 3600 V~
- UL registered, E 72873
- Gate-cathode twin pins for version 1B

### Applications

- DC motor control
- Softstart AC motor controller
- Light, heat and temperature control

### Advantages

- Space and weight savings
- Simple mounting with two screws
- Improved temperature and power cycling
- Reduced protection circuits

Symbol	Test Conditions	Characteristic Values		
$I_{RRM}, I_{DRM}$	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	3	mA	
$V_T, V_F$	$I_T, I_F = 80 \text{ A}; T_{VJ} = 25^\circ\text{C}$	1.64	V	
$V_{TO}$	For power-loss calculations only ( $T_{VJ} = 125^\circ\text{C}$ )			0.85 V
$r_T$		11.0	$\text{m}\Omega$	
$V_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	1.5	V	
$I_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	1.6	V	
		100	mA	
		200	mA	
$V_{GD}$	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	0.2	V	
$I_{GD}$		10	mA	
$I_L$	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}; V_D = 6 \text{ V}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	450	mA	
$I_H$	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	200	mA	
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	2	$\mu\text{s}$	
$t_q$	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}, t_p = 200 \mu\text{s}; -di/dt = 10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 20 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ.	150	$\mu\text{s}$
$Q_s$	$T_{VJ} = T_{VJM}; I_T, I_F = 25 \text{ A}, -di/dt = 0.64 \text{ A}/\mu\text{s}$	50	$\mu\text{C}$	
$I_{RM}$		6	A	
$R_{thJC}$	per thyristor/diode; DC current	{ other values see Fig. 8/9 }	0.88	K/W
	per module		0.44	K/W
$R_{thJK}$	per thyristor/diode; DC current		1.08	K/W
	per module		0.54	K/W
$d_s$	Creepage distance on surface	12.7	mm	
$d_A$	Strike distance through air	9.6	mm	
$a$	Maximum allowable acceleration	50	$\text{m}/\text{s}^2$	

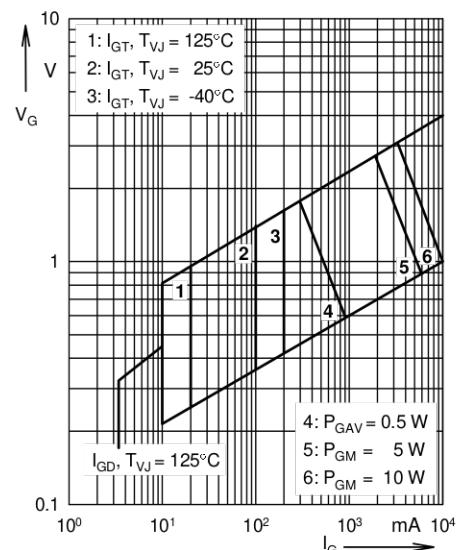


Fig. 1 Gate trigger characteristics

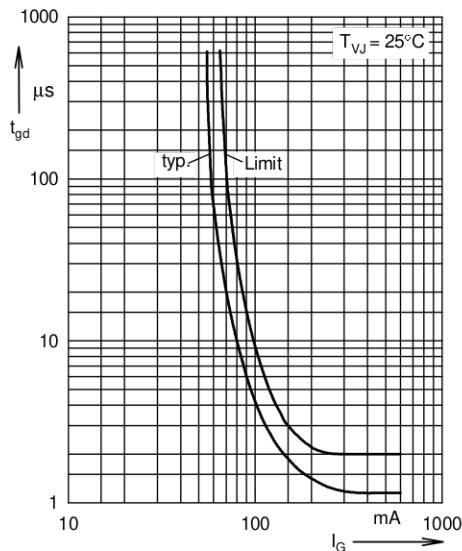
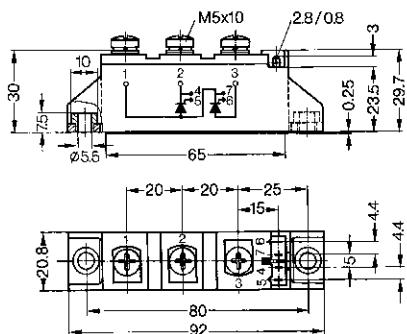


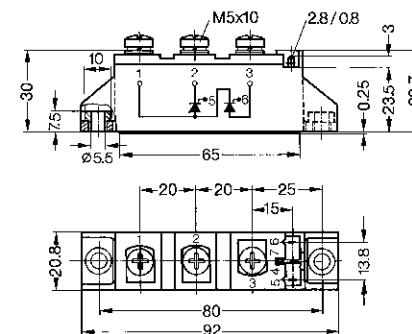
Fig. 2 Gate trigger delay time

**Dimensions in mm (1 mm = 0.0394")**

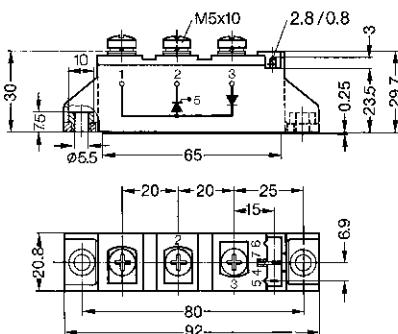
MCC Version 1 B



MCC Version 8 B



MCD Version 8 B



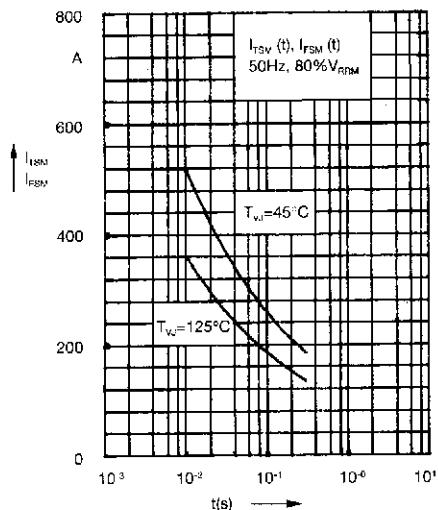


Fig. 3 Surge overload current  
 $I_{TSM}, I_{FSM}$ : Crest value,  $t$ : duration

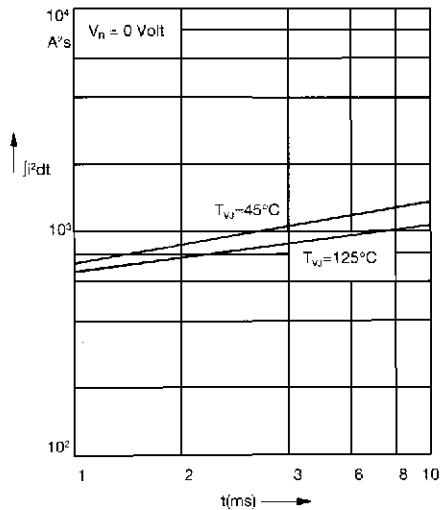


Fig. 4  $j^2dt$  versus time (1-10 ms)

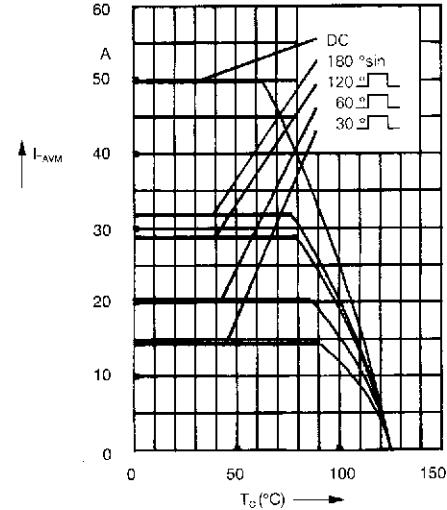


Fig. 4a Maximum forward current at case temperature

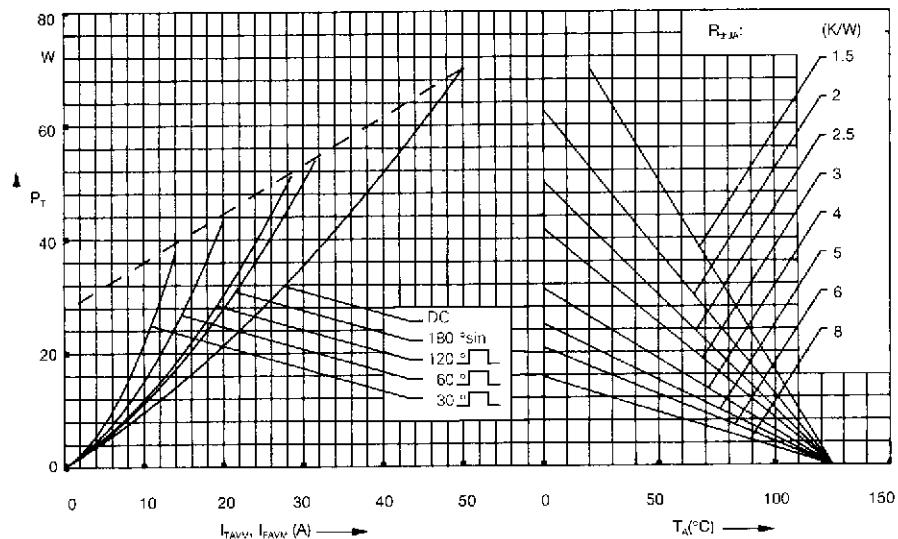


Fig. 5 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

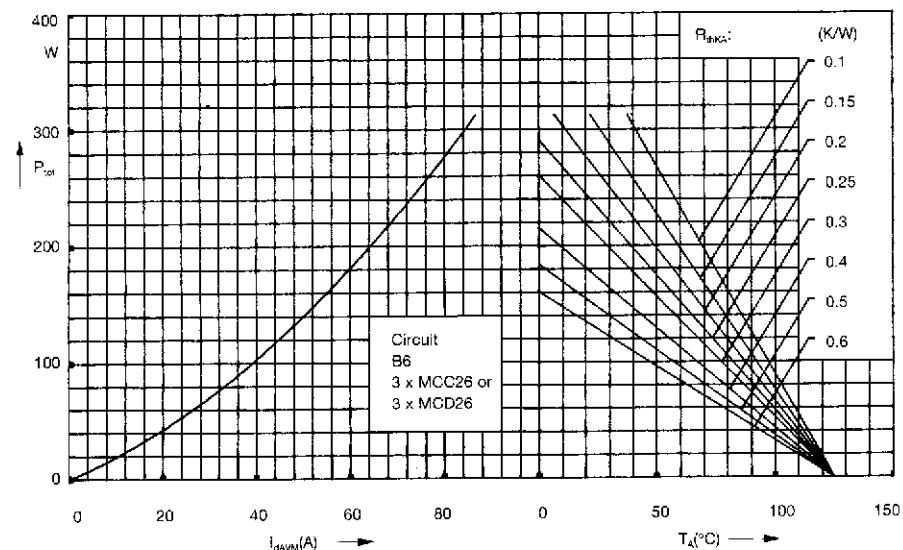


Fig. 6 Three phase rectifier bridge:  
Power dissipation versus direct output current and ambient temperature

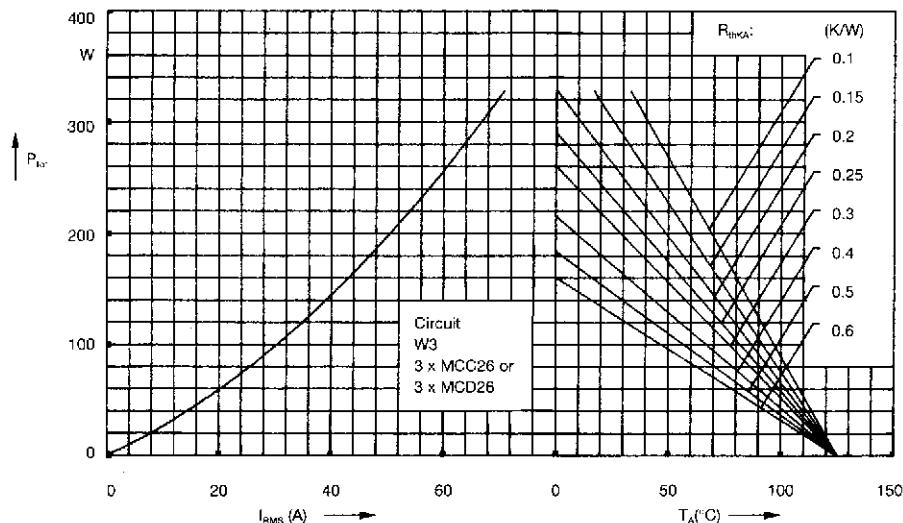


Fig. 7 Three phase AC-controller:  
Power dissipation versus RMS  
output current and ambient  
temperature

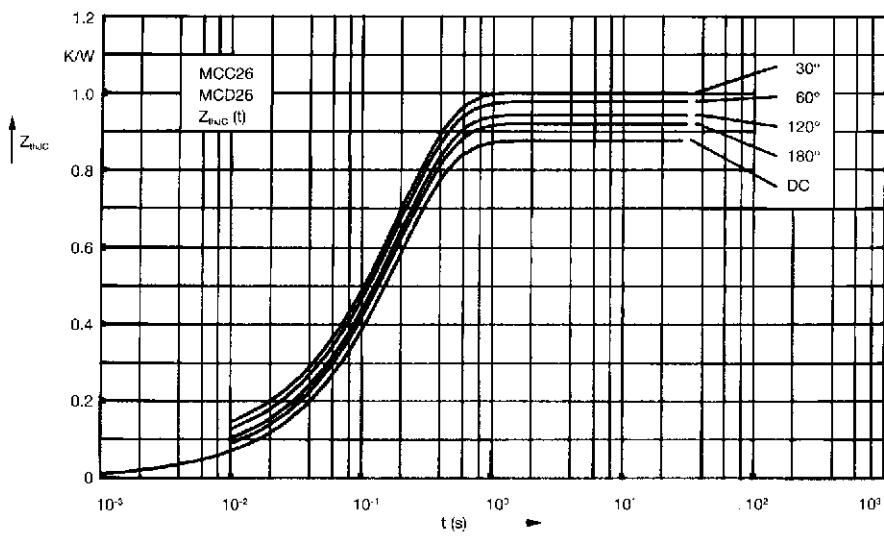


Fig. 8 Transient thermal impedance  
junction to case (per thyristor or  
diode)

$R_{thJC}$  for various conduction angles d:

d	$R_{thJC}$ (K/W)
DC	0.88
180°	0.92
120°	0.95
60°	0.98
30°	1.01

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.019	0.0031
2	0.029	0.0216
3	0.832	0.191

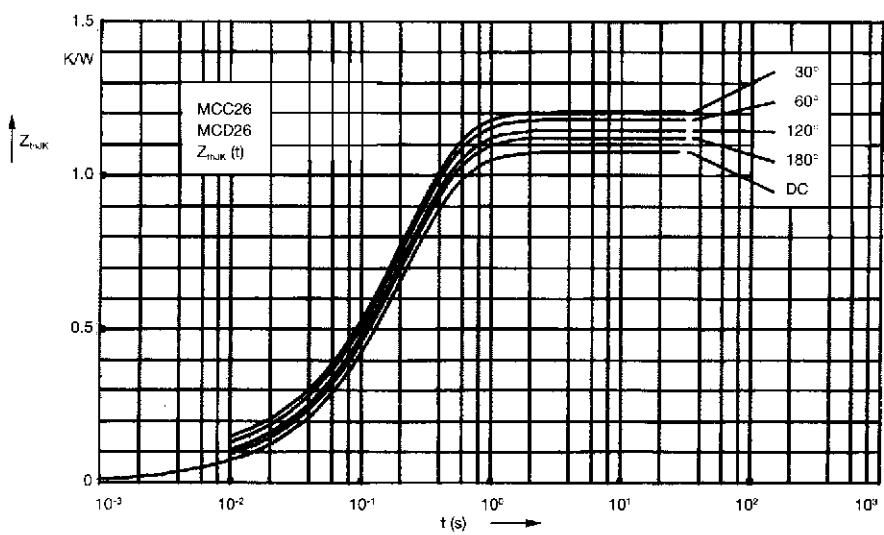


Fig. 9 Transient thermal impedance  
junction to heatsink (per thyristor or  
diode)

$R_{thJK}$  for various conduction angles d:

d	$R_{thJK}$ (K/W)
DC	1.08
180°	1.12
120°	1.15
60°	1.18
30°	1.21

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.019	0.0031
2	0.029	0.0216
3	0.832	0.191
4	0.2	0.45